

MK SD NAND Product Datasheet

Industrial Grade

Product List

MKDV1GIL-AS / MKDV2GIL-AS MKDV4GIL-AS / MKDV8GIL-AS

http://www.mkfounder.com



Revision History

Version	Date	Description
Rev 1.0	2018/4/20	Original version
Rev 1.2	2019/2/15	Operating Temperature
Rev 1.3	2019/9/27	SPI Mode Pin Assignment

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1 Introduction

MK SD NAND is an embedded storage solution designed in a LGA package form. The operation of SD is similar to an SD card which is an industrial standard.

SD NAND consists of NAND flash and a high performance controller. 3.3V supply voltage is required for the NAND area (VCC).

SD NAND is fully compliant with SD2.0 interface, which allows most of general CPU to utilize.

SD NAND has high performance, high quality and low power consumption.

2 Product List

Part No.	Actual Capacity	Package	Size
MKDV1GIL-AS	118MByte	LGA-8	6x8mm
MKDV2GIL-AS	239MByte	LGA-8	6x8mm
MKDV4GIL-AS	482MByte	LGA-8	6x8mm
MKDV8GIL-AS	964MByte	LGA-8	6x8mm

3 Features

- Support up to 50Mhz clock frequency
- SD-protocol compatible
- Supports SPI Mode
- Built-in HW ECC Engine and highly reliable NAND management mechanism
- Write speed up to class 6
- Smaller package LGA-8



4 Physical Characteristics

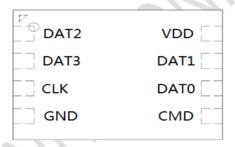
4.1 Temperature

1) Operation Conditions Temperature Range: $Ta = -40^{\circ}C$ to $85^{\circ}C$

2) Storage Conditions
Temperature Range: Tstg = −65°C to 150°C

5 Pin Assignments(SD Mode& SPI Mode)

TOP VIEW



		SD Mode		SPI Mode			
Name	Tyte	Description	Description Tyte Des				
DAT2	I/O/PP	Data Line [Bit 2]	RSV	Reserved			
DAT3	I/O/PP	Data Line [Bit 3]	13	Chip Select (neg true)			
CLK	I	Clock	I	Clock			
GND	S	Supply voltage ground	S	Supply voltage ground			
VDD	S	Supply voltage	S	Supply voltage			
DAT1	I/O/PP	Data Line [Bit 1]	RSV	Reserved			
DAT0	I/O/PP	Data Line [Bit 0]	O/PP	Data Out			
CMD	PP	Command/Response	I	Data In			



- a. Type Key: S=power supply; I= input; O=output using push-pull drivers; PP=I/O using push-pull drivers.
- b. The extended DAT lines (DAT1-DAT3) are input on power up. They start to operate as DAT lines after the SET_BUS_WIDTH Type Key: S=power supply; I=input; O=output using push-pull drivers; PP=I/O using push-pull drivers.
- c. At power up this line has a 50 kilohm pull-up enabled in the card. This resistor serves two functions: Card detection and Mode Selection. For Mode Selection, the host can drive the line high or let it be pulled high to select SD mode. If the host wants to select SPI mode it should drive the line low. For Card detection, the host detects that the line is pulled high. This pull-up should be disconnected by the user, during regular data transfer, with SET_CLR_CARD_DETECT (ACMD42) command.

6 Usage

6.1 SD Bus Mode protocol

The SD bus allows the dynamic configuration of the number of data line from 1 to 4 Bi-directional data signal. After power up by default, the SD card will use only DAT0. After initialization, host can change the bus width.

Multiplied SD cards connections are available to the host. Common VDD, VSS and CLK signal connections are available in the multiple connections. However, Command, Respond and Data lined (DAT0-DAT3) shall be divided for each device from host.

This feature allows easy trade off between hardware cost and system performance. Communication over the SD bus is based on command and data bit stream initiated by a start bit and terminated by stop bit.

Command

Commands are transferred serially on the CMD line. A command is a token to starts an operation from host to the device. Commands are sent to an addressed single card (addressed Command) or to all connected cards (Broad cast command).

Response

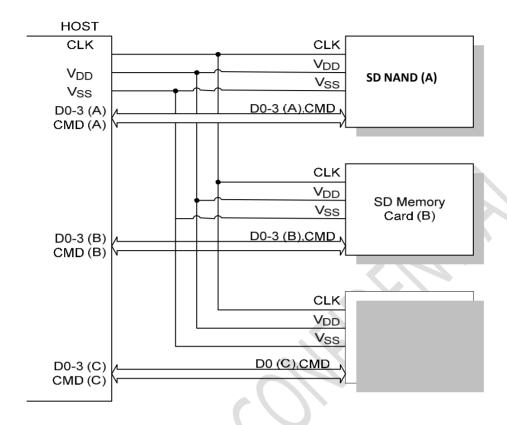
Responses are transferred serially on the CMD line.

A response is a token to answer to a previous received command. Responses are sent from an addressed single card or from all connected cards.

Data

Data can be transfer from the card to the host or vice versa. Data is transferred via the data lines.





CLK	Host card Clock signal
CMD	Bi-directional Command/ Response Signal
DATO-DAT3	4 Bi-directional data signal
VDD	Power supply
VSS	GND



6.2 Card Initialize

To initialize the SD NAND, follow the following procedure is recommended example.

1) Supply Voltage for initialization

Host System can apply the Operating Voltage from initialization to the card. Apply more than 74 cycles of Dummy-clock to the SD card.

2) Select operation mode (SD mode or SPI mode)

In case of SPI mode operation, host should drive 1 pin (CD/DAT3) of SD Card I/F to "Low" level. Then, issue CMD0. In case of SD mode operation, host should drive or detect 1 pin of SD Card I/F (Pull up register of 1 pin is pull up to "High" normally).

Card maintain selected operation mode except re-issue of CMD0 or power on below is SD mode initialization procedure.

- 3) Send the ACMD41 with Arg = 0 and identify the operating voltage range of the Card.
- 4) Apply the indicated operating voltage to the card.

Reissue ACMD41 with apply voltage storing and repeat ACMD41 until the busy bit is cleared. (Bit 31 Busy = 1) If response time out occurred, host can recognize not SD Card.

- 5) Issue the CMD2 and get the Card ID (CID).
- 6) Issue the CMD3 and get the RCA. (RCA value is randomly changed by access, not equal zero)
- 7) Issue the CMD7 and move to the transfer state.

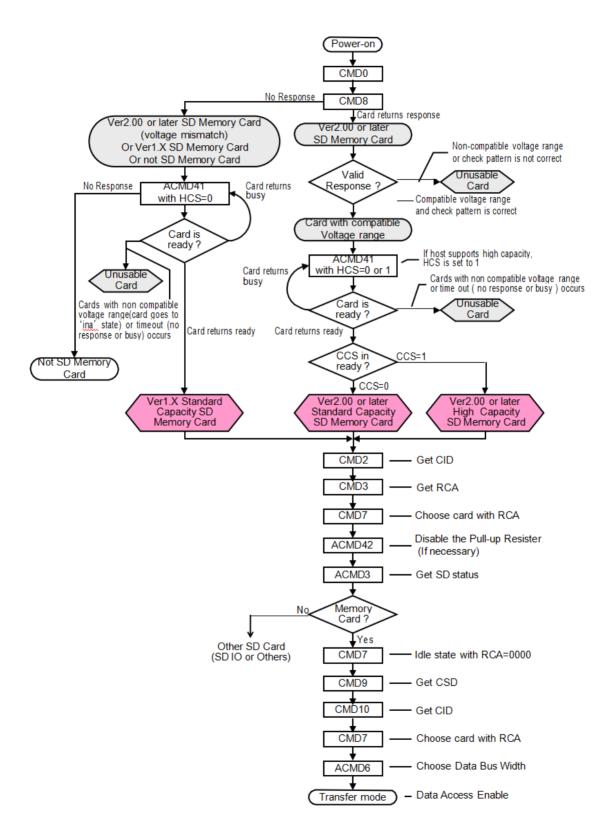
If necessary, Host may issue the ACMD42 and disabled the pull up resistor for Card detect.

- 8) Issue the ACMD13 and poll the Card status as SD Memory Card.Check SD_CARD_TYPE value. If significant 8 bits are "all zero", that means SD Card. If it is not, stop initialization.
- 9) Issue CMD7 and move to standby state. Issue CMD9 and get CSD. Issue CMD10 and get CID.
- 10) Back to the Transfer state with CMD7.
- 11) Issue ACMD6 and choose the appropriate bus-width.

Then the Host can access the Data between the SD card as a storage device.



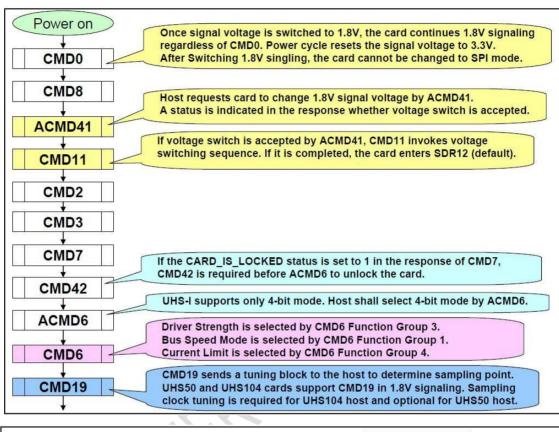
Normal SD initial flow

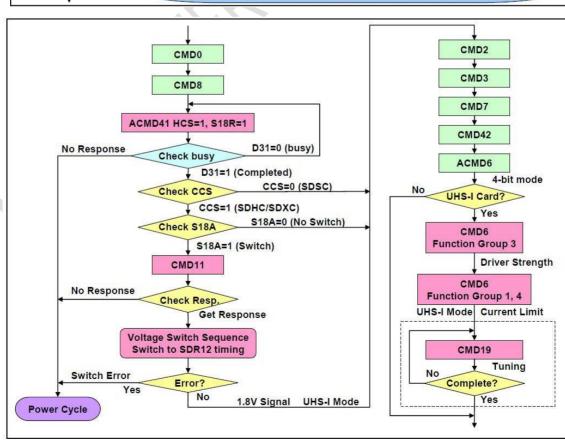


SD card Initialize Procedure



SD3.0 initial flow for UHS-I(IO 1.8v) switch







6.3 DC Characteristics

DC Characteristics

lte	em	Symbol	MIN.	MAX.	Unit	Note	
Supply Voltag	ge	VDD	2.7	3.6	V		
Input	High Level	VIH	VDD×0.625	VDD+0.3	V		
Voltage	Low Level	VIL	VSS-0.3	V _{DD} ×0.25	V		
Output	High Level	Vон	VDD×0.75	_	V	IOH = -2mA, VDD=VDD min	
Voltage	Voltage Low Level VO		_	VDD×0.125	V	IOL = 2mA, VDD=VDD min	
			1	0.25 (32Gb)		VDD = 3.6V , Clock 25MHz	
Standby Curr	Standby Current		_	0.05	mA	VDD = 3.3V, Clock STOP, Ta=25 $^{\circ}$ C	
Operation	Write	ICC2	1	30 (32Gb)		2.27/25841- 50841-	
Current (*)	Current (*) Read		_	28 (32Gb)	mA	3.3V / 25MHz, 50MHz	
Input Voltage	Setup Time	Vrs	_	250	ms	From 0V to VDD min	

^{*)} Peak Current: RMS value over a 10usec period

Peak Voltage and Leak Current

Item	Symbol	Min.	Max.	Unit	Note
Peak voltage on all lines		-0.3	VDD+0.3	V	
Input Leakage Current for all pins		-10	10	uA	
Output Leakage Current for all outputs		-10	10	uA	

Signal Capacitance

Item	Symbol	Min.	Max.	Unit	Note
Pull up Resistance	RCMD RDAT	10	100	kΩ	
Total bus capacitance for each signal line	CL	_	40	pF	1 card CHOST+CBUS≦30pF
Card capacitance for signal pin	CCARD	_	10	pF	
Pull up Resistance inside card (pin1)	RDAT3	10	90	$\mathbf{k}\Omega$	
Capacity Conneted to Power line	CC	_	5	uF	



7 Internal Information

7.1 Registers

The SD NAND has six registers and SD Status information: OCR, CID, CSD, RCA, DSR, SCR and SD Status. DSR IS NOT SUPPORTED in this card.

There are two types of register groups.

MMC compatible registers: OCR, CID, CSD, RCA, DSR, and SCR SD card Specific: SD Status

SD card Registers

Resister Name	Bit Width	Description
OCR	32	Operation Conditions (VDU Voltage Profile and Busy Status
CID	128	Card Identification information
CSD	128	Card specific information
RCA	16	Relative Card Address
DSR	16	Not Implemented (Programmable Card Driver): Driver Stage Register
SCR	64	SD Memory Card "s special features
SD Status	512	Status bits and Card features



7.1.1 OCR Register

This 32-bit register describes operating voltage range and status bit in the power supply.

OCR register definition

	l	1 10 1				
OCR	VDD voltage window	Initial				
bit	VDD voitage willdow	32Gb 64Gb				
21	Courd to account on a statute hit/houses	"0" =				
31	Card power up status bit(busy)	busy,				
		"1" =				
20	Cond Connecting Class	"0" = SD				
30	Card Capacity Status	Memory				
		Card				
29-25	reserved	All "0"				
24	Switching to 1.8V Accepted(S18A)	0				
23	3.6-3.5	1				
22	3.5 - 3.4	1				
21	3.4 - 3.3	1				
20	3.3 - 3.2	1				
19	3.2 - 3.1	1				
18	3.1 - 3.0	1				
17	3.0 - 2.9	1				
16	2.9 - 2.8	1				
15	2.8 - 2.7	1				
14	Reserved	0				
13	Reserved	0				
12	Reserved	0				
11	Reserved	0				
10	Reserved	0				
9	Reserved	0				
8	Reserved	0				
7	Reserved for Low Voltage Range	0				
6	Reserved	0				
5	Reserved	0				
4	Reserved	0				
3-0	reserved	All 0				

bit 23-4: Describes the SD Card Voltage

bit 31 indicates the card power up status. Value "1" is set after power up and initialization procedurehas been completed.



7.1.2 CID Register

The CID (Card Identification) register is 128-bit width. It contains the card identification information. (Refer Appendix 3. for the detail)

The Value of CID Register is vender specific.

CID Register

		II	Initial Value				
Field	Width	CID-slice		32Gb	64Gb		
MID	8	[127:120]		TB			
OID	16	[119:104]		TBD			
PNM	40	[103:64]	TBD	TBD	TBD	-	
PRV	8	[63:56]	TB				
PSN	32	[55:24]		(a) (Product	serial number)		
-	4	[23:20]		All	"0b"		
MDT	12	[19:8]	(a) (Manufacture date)				
CRC	7	[7:1]	(b) (CRC)				
-	1	[0:0]		1b			

- a. Depends on the SD Card. Controlled by Production Lot.
- b. Depends on the CID Register



7.1.3 CSD Register

CSD is Card-Specific Data register provides information on 128bit width. Some field of this register can writable by PROGRAM_CSD (CMD27).

CSD Register

	C5D Register							
		Cell	CSD		Initial	Value		
Field	Width	Туре	Slice		32Gb	64Gb		
CSD_STRUCTURE	2	R	[127:126]	01b				
-	6	R	[125:120]		All "	0b"		
TAAC	8	R	[119:112]		0_0001_1	110b (1ms)		
NSAC	8	R	[111:104]		00000	0000		
TRAN_SPEED	8	R	[103:96]		0_0110_0	10b		
CCC	12	R	[95:84]		0101_10	011_0101		
READ_BL_LEN	4	R	[83:80]		1001	0		
READ_BL_PARTIAL	1	R	[79:79]		0b			
WRITE_BLK_MISALIG	1	R	[78:78]		0b			
READ_BLK_MISALIGN	1	R	[77:77]		0b			
DSR_IMP	1	R	[76:76]		0b			
-	6	R	[75:70]		All "	0b"		
C_SIZE	22	R	[69:48]	TBD	TBD	TBD		
-	1	R	[47:47]		0b			
ERASE_BLK_EN	1	R	[46:46]		1b			
SECTOR_SIZE	7	R	[45:39]		11_1:	111_1		
WP_GRP_SIZE	7	R	[38:32]		000_0	0000		
WP_GRP_ENABLE	1	R	[31:31]		0b			
-	2	R	[30:29]		00b			
R2W_FACTOR	3	R	[28:26]		010b			
WRITE_BL_LEN	4	R	[25:22]		1001	0		
WRITE_BL_PARTIAL	1	R	[21:21]		0b			
-	2	R	[20:16]		All "	0b"		
FILE_FORMAT_GRP	1	R (1	[15:15]		0b			
COPY	1	R/W,	[14:14]		0b			
PERM_WRITE_PROTE	1	R/W	[13:13]	0b				
TMP_WRITE_PROTEC	1	R/W	[12:12]	0b				
FILE_FORMAT	2	R	[11:10]	00b				
-	2	R	[9:8]	All "0b"				
CRC	7	R/W	[7:1]		(CRC)			
-	1	-	[0:0]		1b			

Cell Type:R: Read Only, R/W: Writable and Readable, R/W(1): One-time Writable / Readable Note: Erase of one data block is not allowed in this card. This information is indicated by "ERASE_BLK_EN".

Host System should refer this value before one data block size erase.



7.1.4 RCA Register

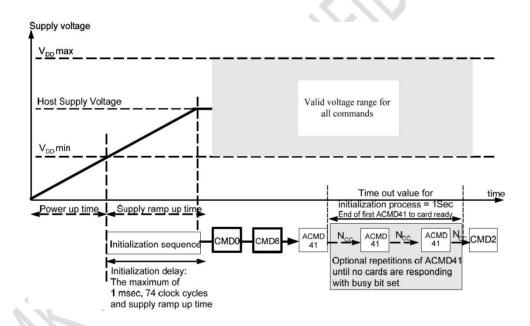
The writable 16bit relative card address register carries the card address in SD Card mode.

7.1.5 DSR Register

This register is not implemented on this car.

8 Power Scheme

8.1 Power Up



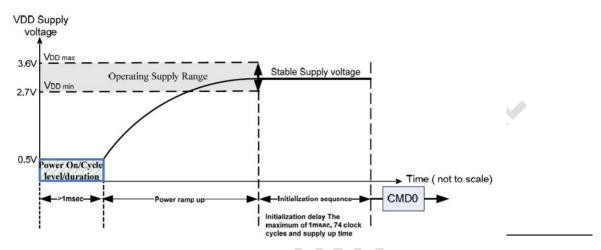
'Power up time' is defined as voltage rising time from 0 volt to VDD min.

'Supply ramp up time' provides the time that the power is built up to the operating level (Host Supply Voltage) and the time to wait until the SD NAND can accept the first command,

The host shall supply power to the card so that the voltage is reached to Vdd_min within 250ms and start to supply at least 74 SD clocks to the SD NAND with keeping CMD line to high.



8.2 Power Up Time



Host needs to keep power line level less than 0.5V and more than 1ms before power ramp up.



8.2.1 Power On or Power Cycle

Followings are requirements for Power on and Power cycle to assure a reliable SD NAND hard reset.

- (1) Voltage level shall be below 0.5V
- (2) Duration shall be at least 1ms.

8.2.2 Power Supply Ramp Up

The power ramp up time is defined from 0.5V threshold level up to the operating supply voltage which is stable between VDD(min.) and VDD(max.) and host can supply SDCLK.

Followings are recommendation of Power ramp up:

- (1) Voltage of power ramp up should be monotonic as much as possible.
- (2) The minimum ramp up time should be 0.1ms.
- (3) The maximum ramp up time should be 35ms for 2.7-3.6V power supply.

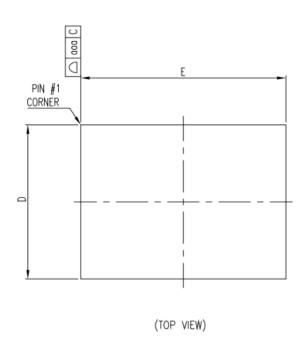
8.2.3 Power Supply Ramp Up

When the host shuts down the power, the VDD shall be lowered to less than 0.5Volt for a minimum period of 1ms. During power down, DAT, CMD, and CLK should be disconnected or driven to logical 0 by the host to avoid a situation that the operating current is drawn through the signal lines.

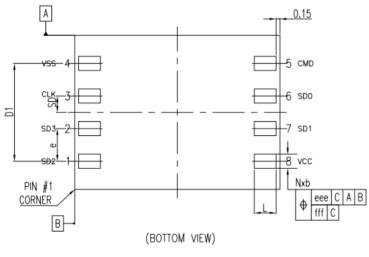
If the host needs to change the operating voltage, a power cycle is required. Power cycle means the power is turned off and supplied again. Power cycle is also needed for accessing cards that are already in Inactive State. To create a power cycle the host shall follow the power down description before power up the card (i.e. the VDD shall be once lowered to less than 0.5Volt for a minimum period of 1ms).



9 Package Dimensions



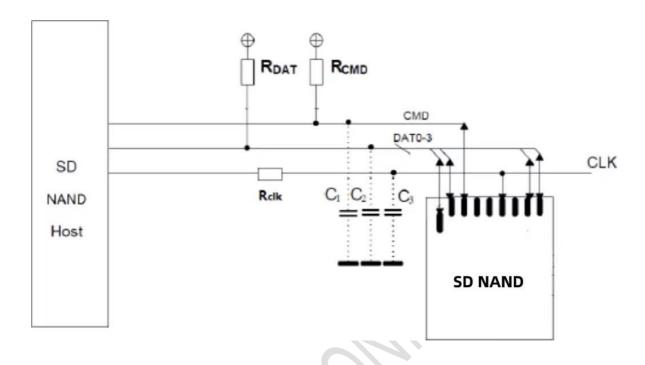




SYMBOL DIMENSION IN MM DIMENSION IN INCH MIN. NOM. MAX. MIN. NOM. MAX. A 0.65 0.70 0.75 0.026 0.028 0.030 b 0.50 0.55 0.60 0.020 0.022 0.024 D 5.90 6.00 6.10 0.232 0.236 0.240 E 7.90 8.00 8.10 0.311 0.315 0.319 L 0.80 0.85 0.90 0.031 0.033 0.035 e 1.27 BSC. 0.050 BSC. JEDEC MO-222(REF.)/MM add 0.08 eee 0.10 ddd 0.08 eee 0.15 fff 0.05 N SE (mm) SD (mm) E1 (mm) D1 (mm) 8 0.635 BSC. 3.81											
MIN. NOM. MAX. MIN. NOM. MAX.		SYMBOL	DIMENSION IN MM				DIMENSION IN INCH				
b 0.50 0.55 0.60 0.020 0.022 0.024 D 5.90 6.00 6.10 0.232 0.236 0.240 E 7.90 8.00 8.10 0.311 0.315 0.319 L 0.80 0.85 0.90 0.031 0.033 0.035 e 1.27 BSC. 0.050 BSC. JEDEC MO-222(REF.)/MM aaa 0.10 bbb 0.10 ddd 0.08 eee 0.15 fff 0.05 N SE (mm) SD (mm) E1 (mm) D1 (mm)			MIN.	MIN. NO		MAX.	MIN.	. NO		M. MAX.	
D 5.90 6.00 6.10 0.232 0.236 0.240 E 7.90 8.00 8.10 0.311 0.315 0.319 L 0.80 0.85 0.90 0.031 0.033 0.035 e 1.27 BSC. 0.050 BSC. JEDEC MO-222(REF.)/MM aaa 0.10 bbb 0.10 ddd 0.08 eee 0.15 fff 0.05 N SE (mm) SD (mm) E1 (mm) D1 (mm)		Α	0.65	0.	70	0.75	0.026	0.0	28	0.030	
E 7.90 8.00 8.10 0.311 0.315 0.319 L 0.80 0.85 0.90 0.031 0.033 0.035 e 1.27 BSC. 0.050 BSC. JEDEC MO-222(REF.)/MM aaa 0.10 bbb 0.10 ddd 0.08 eee 0.15 fff 0.05 N SE (mm) SD (mm) E1 (mm) D1 (mm)		b	0.50	0.	55	0.60	0.020	0.0	22	0.024	
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e 1.27 BSC. 0.050 BSC. JEDEC MO-222(REF.)/MM aaa 0.10 bbb 0.10 ddd 0.08 eee 0.15 fff 0.05 N SE (mm) SD (mm) E1 (mm) D1 (mm)		Ε	7.90	8.	00	8.10	0.311	0.315		0.319	
JEDEC MO-222(REF.)/MM aaa 0.10 bbb 0.10 ddd 0.08 eee 0.15 fff 0.05 N SE (mm) SD (mm) E1 (mm) D1 (mm)		L	0.80	0.	85	0.90	0.031	0.033		0.035	
aga 0.10 bbb 0.10 ddd 0.08 eee 0.15 fff 0.05 N SE (mm) SD (mm) E1 (mm) D1 (mm)		е	1.27 BSC.				0.050 BSC.				
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ddd 0.08 eee 0.15 fff 0.05 N SE (mm) SD (mm) E1 (mm) D1 (mm)		aaa	0.10								
eee 0.15 fff 0.05 N SE (mm) SD (mm) E1 (mm) D1 (mm)		bbb	0.10								
fff 0.05 N SE (mm) SD (mm) E1 (mm) D1 (mm)		ddd	0.08								
N SE (mm) SD (mm) E1 (mm) D1 (mm)		eee	0.15								
1, 55 (1111) 55 (1111) 51 (1111)		fff	0.05								
8 0.635 BSC 3.81 BSC.	İ	Ŋ	SE (mm)		SD (mm)		E1 (mm)		D1 (mm)		
		8			0.6	35 BSC.			3.8	B1 BSC.	



10 Reference Design



RDAT and RCMD (10K \sim 100 k Ω) are pull-up resistors protecting the CMD and the DAT lines against bus floating when SD NAND is in a high-impedance mode.

The host shall pull-up all DAT0-3 lines by RDAT, even if the host uses the SD NAND as 1 bit mode-only in SD mode. It is recommended to have 2.2uF capacitance on VDD. Rclk reference $0\sim120~\Omega$.